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Graphene and Carbon Nanotubes

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 k_{v}

Why do we need nano-materials? Carbon Nanotubes and Graphene are Important For Motivating the Nanoworld

- The Shrinking of Electronics and Moore's Law
- Rapid advances in molecular Biology at the nanoscale
- Evolution of Materials Chemistry from a molecule to a quantum dot



Moore's Law



Biology at the nanoscale

Molecule quantum dot

Moore's Law For Semiconductor Electronics Soon, All Microchips Will Be nanoscale Devices



Semiconductor devices were approaching the nano scale when nanotubes had their official birthday.

Semiconductor Research Corporation

Biological Building Blocks in the Nanoworld

Artist's conception of a DNA strand being packed inside a virus capsid by a molecular motor. The rotary motor of the virus exerts a force of 60 pN to compress the DNA to 6000 times its normal volume. The internal pressure thus generated is later used by the virus to launch this DNA into a cell.



(Credit: C. Bustamante, UCBerkeley)

A Potential Quantum Dot Building Block For Electronics Applications



 Left: Lithographically-patterned coupled quantum dot molecule formed in a GaAs/AlGaAs heterostructure. Using voltages applied to the gates, a double-well potential is created where individual electrons can be trapped in the left or right hand well. The charge state of the molecule is read out using the quantum point contact of the confining gates as a sensor. Right: Measured "phase diagram" of the molecule, where (nL,nR) indicates the number of electrons in the left and right wells. The slanted lines indicate places where the charge state changes. (Credit: C. Marcus, Harvard U.)

Carbon Nanotubes - a Prototype 1D (one-dimensional) material of the Nanoworld



Left: Electron spiraling down a nanotube. The nanotube energy levels are quantized, as in an atom, so that every (n,m) nanotube species has a different fluorescence peak energy determined by its diameter and chirality, as shown in the right panel. (Credits: left, P. McEuen, Cornell U; right, R.B. Weisman, Rice U)

Carbon Allotropes with various dimensions



Hill, J. W., and Petrucci, R. H., *General Chemistry*, 3rd edition, Prentice Hall, NJ, (2002)



Family of carbon

hybridization and geometry R. Saito, in "Carbon Alloy" Elsevier (2003)



- sp³: Diamond (3D)
 - sp²: Graphite (2D)

sp: Carbyne (1D)

- Fullerene (0D)
- Fullerene Polymer(1-3D) Nanotube (1D) Peapod (0D+1D)





glassy, whisker, fiber, nanohorn, turbostratic, ribbon

Not crystal: HOPG, VGCF,



ribbon









Peapod

Nanotube Structure

Rolling graphene into a cylinder Chiral vector: $C_h = na_1 + ma_1 \equiv (n,m)$

Physical properties depend on (n,m):

 $d_{t} = \sqrt{3}a_{C-C}(n^{2} + m^{2} + nm)^{1/2} / \pi$ **Diameter** $n-m = \begin{cases} 3p & \text{metal} \\ 3p \pm 1 & \text{semiconductor} \end{cases}$ **Chirality** $\theta = \tan^{-1} \left(\frac{\sqrt{3}m}{2n+m}\right)$







Shigeo MARUYAMA's Fullerene and Nanotube Site



Arc Method:(by Y. Saito)

18 years of Carbon Nanotubes

S. lijima, (1991), M. S. Dresselhaus *et al.* (1991) J. Mintmire *et al.*, R. Saito *et al.*, N. Hamada *et al*, K. Tanaka *et al*,



Laser Ablation:(by H. Kataura)



Carbon Nanotubes & Graphene both are rapidly growing fields

- Nanotube publications go back to 1952
- Graphene publications go back to 1947
- Number of nanotube publications is still growing rapidly



Why now graphene?

- High performance nano-device
 - high mobility 100,000cm²/Vs at 300K
 - Improvement of nanotechnology
 - Fabricated easier than nanotubes
 - Long spin coherence μm
 - Exotic physics (QHE) at 300K
 - Stable, chemically inactive
- Challenge for graphene devices
 - Integration, process technique
 - Synthesis (SiC, CVD, Scotch tape)
 - Opening energy gap, Edges, defects

Graphene

- = single layer of graphite
- = 2D graphite











Quantum Hall Effect of Graphene









Hall Effect in 1878

In a magnetic field





Quantum Hall Effect in 1980

VOLUME 45, NUMBER 6

PHYSICAL REVIEW LETTERS

11 August 1980

New Method for High-Accuracy Determination of the Fine-Structure Constant Based on Quantized Hall Resistance

K. v. Klitzing

Physikalisches Institut der Universität Würzburg, D-8700 Würzburg, Federal Republic of Germany, and Hochfeld-Magnetlabor des Max-Planck-Instituts für Festkörperforschung, F-38042 Grenoble, France



Quantum Hall Effect



QHE of Graphene in 2005

 $\sigma_{yx} = (n+1/2) [4e^2/h]$



Nature 438 (2005) 04233, 04235





Half-integer quantum Hall effect Zheng-Ando, Gusynin-Sharapov, Peres et al.

Additional Quantum Hall Plateaus

PRL 96, 136806 (2006)

PHYSICAL REVIEW LETTERS

week ending 7 APRIL 2006

Landau-Level Splitting in Graphene in High Magnetic Fields

Y. Zhang,¹ Z. Jiang,^{1,3} J. P. Small,¹ M. S. Purewal,¹ Y.-W. Tan,¹ M. Fazlollahi,¹ J. D. Chudow,¹ J. A. Jaszczak,⁴ H. L. Stormer,^{1,2} and P. Kim¹

¹Department of Physics and Department of Applied Physics, Columbia University, New York, New York 10027, USA ²Bell Labs, Lucent Technologies, Murray Hill, New Jersey 07974, USA ³National High Magnetic Field Laboratory, Tallahassee, Florida 32310, USA ⁴Department of Physics, Michigan Technological University, Houghton, Michigan 49931, USA (Received 1 January 2006; published 6 April 2006)





Valley and spin splitting in the strong field limit

Graphene Quantum Hall Ferromagnet

PRL 96, 256602 (2006)

PHYSICAL REVIEW LETTERS

week ending 30 JUNE 2006

Quantum Hall Ferromagnetism in Graphene

Kentaro Nomura and Allan H. MacDonald Department of Physics, University of Texas at Austin, Austin, Texas 78712-1081, USA (Received 4 April 2006; published 28 June 2006)





QHE in zero-field limit

"Non-relativistic"

"Relativistic"



QHE: Localization in B-fields



Localization and QHE



Singularity at Dirac point

K-K' decoupled case (long-range potential)

QHE of Dirac fermions in $B \rightarrow 0$

 e^{2} σ_{xy} 2h



(per valley, per spin)



Phys. Rev. Lett. 100, 246806 (2008)

Why are nanotube and graphene special?

- 1.Quantum effect at 300K
- 2.Constant Fermi velocity $v_F = c/300$
- 3. Large variety of geometries more than 300.



Hexagons make graphene special.

Similarity to elementary particle physics



A and B carbon atoms in graphene ○



Lattice Structure of Graphene 2 fold symmetry between A and B Two component wave function

$$\Psi(\mathbf{r}) = \begin{pmatrix} \Psi_{\rm A}(\mathbf{r}) \\ \Psi_{\rm B}(\mathbf{r}) \end{pmatrix}$$

Pseudo spin



Pseudo Spin vs Real Spin



$$\begin{split} \Psi(\mathbf{r}) &= \begin{pmatrix} \Psi_{\mathrm{A}}(\mathbf{r}) \\ \Psi_{\mathrm{B}}(\mathbf{r}) \end{pmatrix} \\ \begin{pmatrix} 1 \\ 0 \end{pmatrix} & \text{only A site} \\ \begin{pmatrix} 0 \\ 1 \end{pmatrix} & \text{only B site} \end{split}$$





Energy Band of Graphene



Schrodinger Eq.

$$E(\mathbf{k})\begin{pmatrix}\Psi_{A}(\mathbf{k})\\\Psi_{B}(\mathbf{k})\end{pmatrix} = \begin{pmatrix}0 & -\gamma_{0}f(\mathbf{k})\\-\gamma_{0}f(\mathbf{k})^{*} & 0\end{pmatrix}\begin{pmatrix}\Psi_{A}(\mathbf{k})\\\Psi_{B}(\mathbf{k})\end{pmatrix} \quad \text{Conduction band}$$
$$\det\begin{pmatrix}E(\mathbf{k}) & \gamma_{0}f(\mathbf{k})\\\gamma_{0}f(\mathbf{k})^{*} & E(\mathbf{k})\end{pmatrix} = 0 \quad E(\mathbf{k}) = \pm\gamma_{0}|f(\mathbf{k})|$$

K and K': Dirac points

valence band

Physical Properties of

 $f(\mathbf{k})$

rbon Nanotube





$$f({f k}_{
m F})=0$$
 K point $f(-{f k}_{
m F})=0$ K' point



Taylor expansion of f(k) around the K point

$$E(\mathbf{k}) \begin{pmatrix} \Psi_A(\mathbf{k}) \\ \Psi_B(\mathbf{k}) \end{pmatrix} = \begin{pmatrix} 0 & -\gamma_0 f(\mathbf{k}) \\ -\gamma_0 f(\mathbf{k})^* & 0 \end{pmatrix} \begin{pmatrix} \Psi_A(\mathbf{k}) \\ \Psi_B(\mathbf{k}) \end{pmatrix}$$

K point $f(\mathbf{k}_{\rm F}) = 0$
 $= \frac{3\gamma_0 a_{\rm cc}}{3} \begin{pmatrix} 0 & k_x - ik_y + \cdots \\ k_x + ik_y + \cdots & 0 \end{pmatrix} \begin{pmatrix} \Psi_A(\mathbf{k}) \\ \Psi_B(\mathbf{k}) \end{pmatrix}$

Hamiltonian around the K point



$$\mathcal{H}_{\mathrm{K}} = \hbar v_{\mathrm{F}} \begin{pmatrix} 0 & k_{x} - ik_{y} \\ k_{x} + ik_{y} & 0 \end{pmatrix} \qquad v_{\mathrm{F}} = \frac{\gamma_{0}a_{\mathrm{CC}}}{\hbar}$$

$$k_x = |\mathbf{k}| \cos \Theta(\mathbf{k})$$
$$k_y = |\mathbf{k}| \sin \Theta(\mathbf{k})$$

$$\begin{pmatrix} 0 & e^{-i\Theta} \\ e^{i\Theta} & 0 \end{pmatrix} \begin{pmatrix} 1 \\ e^{i\Theta} \end{pmatrix} = \begin{pmatrix} 1 \\ e^{i\Theta} \end{pmatrix}$$
$$\begin{pmatrix} 0 & e^{-i\Theta} \\ e^{i\Theta} & 0 \end{pmatrix} \begin{pmatrix} 1 \\ -e^{i\Theta} \end{pmatrix} = -\begin{pmatrix} 1 \\ -e^{i\Theta} \end{pmatrix}$$

$$\mathcal{H}_{\mathrm{K}} = \hbar v_{\mathrm{F}} |\mathbf{k}| \begin{pmatrix} 0 & e^{-i\Theta(\mathbf{k})} \\ e^{+i\Theta(\mathbf{k})} & 0 \end{pmatrix}$$

Eigenvalue

Eigenvector

$$E(\mathbf{k}) = \pm \hbar v_{\mathbf{F}} |\mathbf{k}| \qquad \Psi(\mathbf{k}) = \begin{pmatrix} 1 \\ \pm e^{i\Theta} \end{pmatrix}$$

The phase of the wavefunction and Berry's phase

T. Ando et al., J. Phys. Soc. Jpn. 67, 2857 (1998)

$$k_{y} \qquad \Psi_{1}(\mathbf{k}) = \begin{pmatrix} 1 \\ e^{+i\Theta(\mathbf{k})} \end{pmatrix} \qquad \Psi_{2}(\mathbf{k}) = \begin{pmatrix} e^{-i\Theta(\mathbf{k})/2} \\ e^{+i\Theta(\mathbf{k})/2} \\ e^{-i\Theta(\mathbf{k})/2} \\ (=e^{-i\Theta(\mathbf{k})/2} \Psi_{1}(\mathbf{k})) \end{pmatrix}$$

$$(=e^{-i\Theta(\mathbf{k})/2} \Psi_{1}(\mathbf{k})$$

$$(=e^{-i\Theta(\mathbf{k})/2} \Psi_{1}(\mathbf{k})$$

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$$(=e^{-i\Theta(\mathbf{k})/2} \Psi_{1}(\mathbf{k})$$

$$(=e^{-i\Theta(\mathbf{k})/2} \\ \Psi_{1}(\mathbf{k}+2\pi) = \Psi_{1}(\mathbf{k}) \qquad \Psi_{2}(\mathbf{k}+2\pi) = -\Psi_{2}(\mathbf{k})$$
We must add the Berry Phase γ : $\Theta \qquad \Theta + \gamma$

$$\gamma(\Theta) = \qquad \pi \qquad 0$$

$$\Psi_{1}(\mathbf{k}+2\pi) = -\Psi_{1}(\mathbf{k}) \qquad \Psi_{2}(\mathbf{k}+2\pi) = -\Psi_{2}(\mathbf{k})$$



Absence of Back scattering

T. Ando et al., J. Phys. Soc. Jpn, 67, 2857 (1998)





A time reversal pair of back scatterimg Cancel scattering amplitude

to each other by the phase difference of π .

Question: what is the field that polarizes Pseudo Spin or Real Spin?

$$\begin{split} \Psi(\mathbf{r}) &= \begin{pmatrix} \Psi_{\mathrm{A}}(\mathbf{r}) \\ \Psi_{\mathrm{B}}(\mathbf{r}) \end{pmatrix} \\ \begin{pmatrix} 1 \\ 0 \end{pmatrix} & \text{only A site} \end{split}$$

only B site

A: Magnetic field *B* $\begin{pmatrix} 1 \\ 0 \end{pmatrix} \text{ up spin}$ $\begin{pmatrix} 0 \\ 1 \end{pmatrix} \text{ down spin}$

Effective Hamiltonian around the K point

When *m*=0

$$\mathcal{H}_L = -c\boldsymbol{\sigma} \cdot \hat{\mathbf{p}}$$
$$\mathcal{H}_R = c\boldsymbol{\sigma} \cdot \hat{\mathbf{p}}$$

$$\begin{aligned} \mathcal{H}_{\mathrm{K}} &= v_{\mathrm{F}} \boldsymbol{\sigma} \cdot \hat{\mathbf{p}} \\ \mathcal{H}_{K'} &= v_{\mathrm{F}} \boldsymbol{\sigma}' \cdot \hat{\mathbf{p}} \\ \end{aligned} \quad \boldsymbol{\sigma}' &= (-\sigma_x, \sigma_y) \end{aligned}$$

Similar Hamiltonian for graphene with pseudo-spin

 σ : operator for pseudo spin

Edge electronic states at the zigag edge of graphene M. Fujita et al, J. Phys. Soc. Jpn. **65** (1996) 1920

Delocalized states:

$$\Psi_{\mathbf{k}}(\mathbf{r}) = e^{i\mathbf{k}\cdot\mathbf{r}} \begin{pmatrix} \Psi_{\mathrm{A}}(\mathbf{k}) \\ \Psi_{\mathrm{B}}(\mathbf{k}) \end{pmatrix}$$
$$\begin{pmatrix} 1 \\ e^{i\Theta(\mathbf{k})} \end{pmatrix} \checkmark$$

Edge states:

Amplitude of WF

Pseudo-spin polarized states

•W.F. has a value only either A or B site.

$$\Psi(\mathbf{r}) = \begin{pmatrix} \Psi_{\rm A}(\mathbf{r}) \\ 0 \end{pmatrix}$$

•Spacialy localized at zigzag edge

$$e^{-\frac{y}{\xi}} \begin{pmatrix} 1\\ 0 \end{pmatrix}$$

Vector potential for pseudo spin K. Sasaki, R. Saito, *Prog. Theor. Phys. Suppl.* 176, 253 (2008)

modification of nearest neighbor interaction

 $\mathcal{H}_{\mathrm{K}} = v_{\mathrm{F}} \boldsymbol{\sigma} \cdot (\mathbf{\hat{p}} + \mathbf{A}^{\mathrm{q}}(\mathbf{r}))$

$$\mathcal{H}_{\mathrm{K}'} = v_{\mathrm{F}} \boldsymbol{\sigma}' \cdot (\mathbf{\hat{p}} - \mathbf{A}^{\mathrm{q}}(\mathbf{r}))$$

 A^q is expressed by $\delta \gamma_0$

Why? modification of off-diagonal element with time reversal symmetry

Analytic solution of zigzag edge states by A^q K. Sasaki et al., J. Phys. Soc. Japan, **75**, 074713 (2006)

tight binding results

A^q field results

up: energy dispersion, down: localization length

$$\frac{E}{v_F} = \frac{\pm |p_x|}{\cosh\left(-\ln(1-c)\right)} + \mathcal{O}(ap_x^2/\hbar)$$
$$\frac{\hbar}{\xi} = p_x \tanh\left(-\ln(1-c)\right) + \mathcal{O}(ap_x^2/\hbar)$$

$$\frac{E}{v_F} = \frac{\pm |p_x|}{\cosh\left(\frac{1}{\hbar}\int_{-\xi_g}^{\xi_g} A_x(y)dy\right)}$$
$$\frac{\hbar}{\xi} = p_x \tanh\left(\frac{1}{\hbar}\int_{-\xi_g}^{\xi_g} A_x(y)dy\right)$$

Zigzag edge vs Armchair edge

K. Sasaki et al., J. Phys. Soc. Japan, 75, 074713 (2006)

Armchair edge

 $A_x(x)$

 \overline{x}

 \boldsymbol{y}

No pseudo-spin polarization \rightarrow no edge states Useful for considering edge states for any edge

Parity anomaly in graphene – origin of the mass – K. Sasaki, R. Saito, J. Phys. Soc. Japan, 77, 054703 (2008)

- 1. Deformation-induce magnetic field
- 2. Coulomb-induce mass term

Electron-phonon interaction is expressed by A^q

K. Sasaki, R. Saito, G. Dresselhaus, M. S. Dresselhaus, H. Farhat, J. Kong, Phys. Rev. B, 77, 245441 (2008)

 $\mathbf{B}^{\mathrm{q}} = \nabla \times \mathbf{A}^{\mathrm{q}}(\mathbf{r})$

 $\mathbf{B} = \nabla \times \mathbf{A}(\mathbf{r})$

Electro-chemical doping and Raman spectrosocpy of single wall carbon nanotubes Farhat *et al.*, *Phys. Rev. Lett.*, 99 145506(2007)

FIG. 1 (color online). (a) Schematic diagram of the experimental setup. The excitation laser shines through the PEO/LiClO₄ polymer electrolyte. (b) An AFM image indicating that the nanotubes are spaced out and are typically isolated from one another.

isolated metallic SWNT
E_F dependent
upshift of TO?

Raman Shift [cm⁻¹

Chiral angle dependence of KA K. Sasaki, R. Saito, et al. Phys. Rev. B, 77, 245441 (2008)

 k_y

 k_x

Κ

Why TO becomes hard for zigzag NT?

Gate voltage dependence of G band Raman spectra

J. S. Park, et al. unpublished

No Electron-phonon int.

Edge states superconductivity of graphene K. Sasaki, et al., *J. Phys. Soc. Japan*, 76, 033702, (2007)

$T_c > 10 \text{K} !?$

Tang *et al.*, Science **292** (01) for SWNT (0.4nm diameter) Takesue *et al.*, PRL **96** (06) for MWNT (10nm diameter)

Two problems

- 1. no $D(E_F)$
- 2. suppression of el-ph interaction

U : repulsive Coulomb interaction

Edge states could overcome the problems.

Eliashberg equation

Energy bandwidth of edge states

 $W = \gamma_n$

K. Sasaki et al., Appl. Phys. Lett., 88, 113110 (2006)

Summary

Edge states: polarized pseudo spin

$$\begin{pmatrix} \Psi_{\rm A} \\ \Psi_{\rm B} \end{pmatrix} = e^{-\frac{x}{\xi}} \begin{pmatrix} 1 \\ 0 \end{pmatrix}$$

Strong electron-phonon interaction superconductivity

Localized

Pseudo Spin and A^q

B

Application of A^q to el-ph interaction

Thank you.

$$v_{\rm F}\boldsymbol{\sigma} \cdot (\mathbf{\hat{p}} + \mathbf{A}(\mathbf{r})) \begin{pmatrix} \psi_A(\mathbf{r}) \\ \psi_B(\mathbf{r}) \end{pmatrix} = E \begin{pmatrix} \psi_A(\mathbf{r}) \\ \psi_B(\mathbf{r}) \end{pmatrix}$$

Sasaki et al., JPSJ75 (2006)

$$v_{\rm F} A_x(\mathbf{r}) = \delta \gamma_0^1(\mathbf{r}) - \frac{1}{2} \left(\delta \gamma_0^2(\mathbf{r}) + \delta \gamma_0^3(\mathbf{r}) \right)$$
$$v_{\rm F} A_y(\mathbf{r}) = \frac{\sqrt{3}}{2} \left(\delta \gamma_0^2(\mathbf{r}) - \delta \gamma_0^3(\mathbf{r}) \right)$$

$$rac{\hbar}{\xi} = p_x anh\left(rac{1}{\hbar} \int_{-\xi_g}^{\xi_g} A_x(y) dy
ight)$$

to appear in J. Phys. Soc. Jpn. (2008)

 ${\stackrel{\scriptstyle 0}{E}} ({
m eV})$

0

Mass from Coulomb interaction

$$v_{\rm F}\boldsymbol{\sigma} \cdot (\mathbf{p} + \mathbf{A}^{\rm q}(\mathbf{r})) + \widehat{m_s}\sigma_z$$
$$\frac{U}{4}(p_n - p_m)\sigma_z = m_{\uparrow}\sigma_z$$
$$\langle n_s(\mathbf{r}) \rangle = \frac{1}{2}\frac{B_z^{\rm q}(\mathbf{r})}{\Phi_0} \operatorname{sign}(m_s)$$
$$\frac{U}{4}(p_n + p_m)\sigma_z = m_{\downarrow}\sigma_z$$

4

Equal densities at A and B atoms

$$p_n = n_{\rm A} - n_{\rm B}$$

Pseudo-spin polarization disappears, and Real-spin is polarized

$$\mathcal{H}_{\rm int} = \frac{U}{8} \sum_{\mathbf{R}_u} (n^2 - m^2 + p_n^2 - p_m^2)$$

 $\begin{array}{c} & & & \\ & & \\ \hline & & \\ \hline & & \\ \end{array} \end{array} \\ = \begin{pmatrix} 1 \\ e^{+i\Theta(\mathbf{k})} \end{pmatrix} \qquad \Psi(k_x) = \begin{pmatrix} 1 \\ 1 \end{pmatrix} \qquad \overleftarrow{\langle -k_x | \mathcal{H}_{imp} | k_x \rangle} \\ & & \\ \hline & \\ \end{array} \\ \\ \mathbf{k} \\ \mathbf{k}$

後方散乱の抑制

多重散乱でも後方散乱が抑制

Nakanishi et al., JPSJ67, 2857(98)

不純物による散乱

Suzuura and Ando, PRB65, 235412(02)

エッジ状態

 $\begin{pmatrix} 1,0 \end{pmatrix} \begin{pmatrix} V & 0 \\ 0 & V \end{pmatrix} \begin{pmatrix} 1 \\ 0 \end{pmatrix} = V$

二成分間の相対位相や大きさの比 (擬スピン)が物性に関係

グラフェンの擬スピンとは何か

 $E\begin{pmatrix}\Psi_L\\\Psi_R\end{pmatrix} = \begin{pmatrix}-c\boldsymbol{\sigma}\cdot\hat{\mathbf{p}} & mc^2I\\mc^2I & c\boldsymbol{\sigma}\cdot\hat{\mathbf{p}}\end{pmatrix}\begin{pmatrix}\Psi_L\\\Psi_R\end{pmatrix}$

ディラック方程式と電磁

まとめ 二成分間の相対位相

実スピン

場

 $\hat{\mathbf{p}} \to \hat{\mathbf{p}} - e\mathbf{A}(\mathbf{r})$ $\mathbf{B} = \nabla \times \mathbf{A}(\mathbf{r})$

後方散乱の抑制 エッジ状態

$$\begin{pmatrix} 1,0 \end{pmatrix} \begin{pmatrix} V & 0 \\ 0 & V \end{pmatrix} \begin{pmatrix} 1 \\ 0 \end{pmatrix} = V$$

 $\mathcal{H}_{\mathrm{K}} = v_{\mathrm{F}} \boldsymbol{\sigma} \cdot (\hat{\mathbf{p}} + \mathbf{A}^{\mathrm{q}}(\mathbf{r}))$ $\mathcal{H}_{\mathrm{K}'} = v_{\mathrm{F}} \boldsymbol{\sigma}' \cdot (\hat{\mathbf{p}} - \mathbf{A}^{\mathrm{q}}(\mathbf{r}))$ $\mathbf{B}^{\mathrm{q}} = \nabla \times \mathbf{A}^{\mathrm{q}}(\mathbf{r})$ 擬スピンをそろえる 場

$$\mathcal{H}^{\mathrm{K}} = v_{\mathrm{F}}\boldsymbol{\sigma} \cdot (\hat{\mathbf{p}} + \mathbf{A}^{\mathrm{q}}(\mathbf{r})) + \frac{g_{\mathrm{on}}}{2}\sigma_{z}\nabla \cdot \mathbf{u}(\mathbf{r}),$$
$$\mathcal{H}^{\mathrm{K}'} = v_{\mathrm{F}}\boldsymbol{\sigma}' \cdot (\hat{\mathbf{p}} - \mathbf{A}^{\mathrm{q}}(\mathbf{r})) + \frac{g_{\mathrm{on}}}{2}\sigma_{z}\nabla \cdot \mathbf{u}(\mathbf{r}),$$

$$v_{\mathrm{F}}(A_x^{\mathrm{q}}(\mathbf{r}), A_y^{\mathrm{q}}(\mathbf{r})) = \frac{g_{\mathrm{off}}}{a_{\mathrm{cc}}}(u_y(\mathbf{r}), -u_x(\mathbf{r})),$$

Ishikawa et al., JPSJ75 (2006)

Sasaki et al., PRB77 (2008)

 $\begin{pmatrix} 1 & 0 \end{pmatrix} \begin{pmatrix} V & 0 \\ 0 & V \end{pmatrix} \begin{pmatrix} 1 \\ 0 \end{pmatrix} = V$

Calculation of G band Raman spectra

G band Raman spectra = Intensity + Spectral width

1. Raman Intensity
$$I(\omega, E_{\rm L})$$
 optical matrix el-ph matrix optical matrix $[I(\omega, E_{\rm L}) = \sum_{j} \left| \sum_{a} \frac{M_{\rm op}(j, b) M_{\rm el-ph}(b, a) M_{\rm op}(a, j)}{\Delta E_{aj} (\Delta E_{aj} - \hbar \omega)} \right|^{2}$
 $\Delta E_{aj} \equiv E_{\rm L} - (E_{a} - E_{j}) - i\gamma$ resonance energy window
Phonon energy
 $\hbar \omega = \hbar \omega^{(0)}_{\rm Original frequency} + \hbar \omega^{(2)}_{\rm Correction frequency Including el-ph coupling}$
2. Spectral width Electron-hole pair creation matrix by el-ph interaction $\left| \frac{|\langle eh(\mathbf{k})| H_{\rm el-ph} | \omega^{(0)} \rangle|^{2}}{\hbar \omega^{(0)} - [E_{e}(\mathbf{k}) - E_{h}(\mathbf{k})] + i\Gamma \atop energy} + i\Gamma \atop f[E_{e}\mathbf{k}) - E_{F}] - f[E_{h}(\mathbf{k}) - E_{F}] \right\}.$
Fermi distribution function energy width (2) Spectral width energy en

a

Spectral width is given by the decay length Γ .

Gate voltage dependence of G band Raman spectra

J. S. Park, et al. unpublished

For LO mode of zigzag tube, Electron-phonon coupling \rightarrow Almost zero

BN nano ribbon

Coulomb interaction in BN ribbon F. Zheng et al. (unpublished)

Energy gap decreases (BN) increases (G) One spin direction appears at E_F

 $U_B = U_N = 7.5 \mathrm{eV}$

$$H = \sum_{i,\sigma} \Delta_i c_{i,\sigma}^+ c_{i,\sigma} + \sum_{\langle i,j \rangle,\sigma} t(c_{i,\sigma}^+ c_{j,\sigma} + c_{j,\sigma}^+ c_{i,\sigma}) + \sum_i U_i \hat{n}_{i,\uparrow} \hat{n}_{i,\downarrow},$$
$$\Delta_i = \begin{cases} \Delta & \text{boron} \\ -\Delta & \text{nitrogen} \end{cases}, \qquad U_i = \begin{cases} U_B & \text{boron} \\ U_N & \text{nitrogen} \end{cases}.$$

Half metalicity in BN ribbon

F. Zheng et al. (unpublished)

Only down spin can flow at N zigzag edge

 Half metalicity

Citation Distribution by year

Year